

K3158-VB Datasheet

N-Channel 150-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
150	0.030 at $V_{GS} = 10$ V	50
	0.033 at $V_{GS} = 6$ V	45

FEATURES

- TrenchFET[®] Power MOSFETs
- 175 °C Junction Temperature
- New Low Thermal Resistance Package
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC

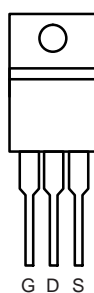


RoHS
COMPLIANT

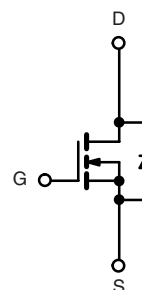
APPLICATIONS

- Primary Side Switch

TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	50
		$T_C = 125$ °C	35
Pulsed Drain Current	I_{DM}	150	A
Avalanche Current	I_{AR}	50	
Repetitive Avalanche Energy ^a	E_{AR}	80	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	166 ^b
		$T_A = 25$ °C ^c	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.9	

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	80			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.030		Ω
		$V_{GS} = 6\text{ V}, I_D = 10\text{ A}$		0.033		
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.076		
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.100		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$	10			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2500		μF
Output Capacitance	C_{oss}			290		
Reverse Transfer Capacitance	C_{rss}			190		
Gate Resistance	R_g			2		Ω
Total Gate Charge ^c	Q_g	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		38	60	nC
Gate-Source Charge ^c	Q_{gs}			13		
Gate-Drain Charge ^c	Q_{gd}			13		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 1.80\text{ }\Omega$ $I_D \equiv 40\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time ^c	t_r			130	200	
Turn-Off Delay Time ^c	$t_{d(off)}$			30	45	
Fall Time ^c	t_f			90	140	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b						
Continuous Current	I_S				40	A
Pulsed Current	I_{SM}				80	
Forward Voltage ^a	V_{SD}	$I_F = 40\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 40\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		100	150	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			5	8	A
Reverse Recovery Charge	Q_{rr}			0.25	0.6	μC

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Output Characteristics



Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current



Capacitance



Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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